

256K/128K SERIAL I²C BUS EEPROM

PRELIMINARY DATA

- COMPATIBLE with I²C EXTENDED ADDRESSING
- TWO WIRE I²C SERIAL INTERFACE, SUPPORTS 400kHz PROTOCOL
- 100,000 ERASE/WRITE CYCLES
- 40 YEARS DATA RETENTION
- SINGLE SUPPLY VOLTAGE
 - 4.5V to 5.5V for M24256 and M24128
 - 2.5V to 5.5V for M24256-W and M24128-W
 - 1.8V to 5.5V for M24256-R and M24128-R
- HARDWARE WRITE CONTROL
- BYTE and PAGE WRITE (up to 64 BYTES)
- BYTE, RANDOM and SEQUENTIAL READ MODES
- SELF TIMED PROGRAMING CYCLE
- AUTOMATIC ADDRESS INCREMENTING
- ENHANCED ESD/LATCH-UP PERFORMANCES

PSDIP8 (BN) 0.25mm Frame 8 8 8 1 1 1 SO8 (MN) SO8 (MW) 150mil Width 200mil Width

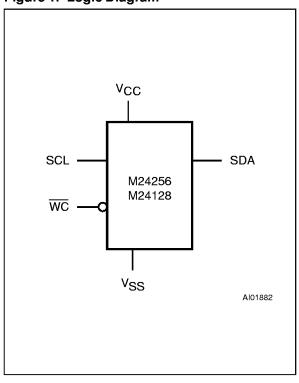
Figure 1. Logic Diagram

DESCRIPTION

The M24256 and the M24128 are a 256K bit and a 128K bit electrically erasable programmable memories (EEPROM), organized as $32,768 \times 8$ and as $16,384 \times 8$ bits respectively. The -W versions operate with a power supply value as low as 2.5V and the -R versions operate down to 1.8V. Both Plastic Dual-in-Line and Plastic Small Outline packages are available.

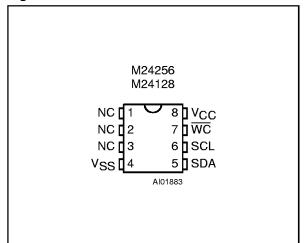
Table 1. Signal Names

SDA	Serial Data Address Input/Output
SCL	Serial Clock
wc	Write Control
Vcc	Supply Voltage
V _{SS}	Ground



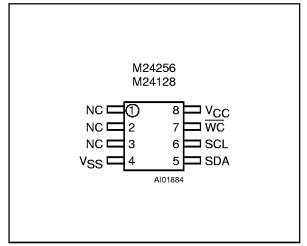
May 1997 1/17

Figure 2A. DIP Pin Connections



Warning: NC = Not Connected

Figure 2B. SO Pin Connections



Warning: NC = Not Connected

Table 2. Absolute Maximum Ratings (1)

Symbol	Pa	Value	Unit		
T _A	Ambient Operating Temperature	•		-40 to 125	°C
T _{STG}	Storage Temperature			-65 to 150	°C
T_{LEAD}	Lead Temperature, Soldering	(SO8) (PSDIP8)	40 sec 10 sec	215 260	°C
V _{IO}	Input or Output Voltages			-0.6 to 6.5	V
V _{CC}	Supply Voltage			-0.3 to 6.5	V
V_{ESD}	Electrostatic Discharge Voltage	(Human Body model)) (2)	4000	V
4 E2D	Electrostatic Discharge Voltage	500	٧		

Notes: 1. Except for the rating "Operating Temperature Range", stresses above those listed in the Table "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the SGS-THOMSON SURE Program and

DESCRIPTION (cont'd)

Each memory is compatible with the I²C extended addressing standard, two wire serial interface which uses a bi-directional data bus and serial clock. The Memory carries a built-in 4 bit, unique device identification code (1010) corresponding to the I²C bus definition. The Memory behaves as a

slave device in the I²C protocol with all memory operations synchronized by the serial clock. Read and write operations are initiated by a START condition generated by the bus master. The START condition is followed by a stream of 4 bits (identification code 1010), then 3 bits (at 000) to form a 7 bit Device Select, plus one read/write bit and terminated by an acknowledge bit.

other relevant quality documents.
2. 100pF through 1500Ω; MIL-STD-883C, 3015.7

^{3. 200}pF through 0Ω; EIAJ IC-121 (condition C)

Table 3. Device Select Code

		Device	Code			Chip Enable	e	RW
Bit	b7	b6	b5	b4	b3	b2	b1	b0
Device Select	1	0	1	0	0	0	0	R₩

Note: The MSB b7 is sent first.

Table 4. Operating Modes

Mode	R₩ bit	Data Bytes	Initial Sequence	
Current Address Read	ddress Read '1' 1 START, Device Select, $R\overline{W}$ = '1'		START, Device Select, RW = '1'	
Random Address Read	,0,	1	START, Device Select, RW = '0', Address,	
Trandom Address Fredd	'1'	'	reSTART, Device Select, $R\overline{W}$ = '1'	
Sequential Read	'1'	≥ 1	As CURRENT or RANDOM Mode	
Byte Write	,0,	1	START, Device Select, RW = '0'	
Page Write	,0,	64	START, Device Select, RW = '0'	

When writing data to the memory it responds to the 8 bits received by asserting an acknowledge bit during the 9th bit time. When data is read by the bus master, it acknowledges the receipt of the data bytes in the same way. Data transfers are terminated with a STOP condition.

Power On Reset: Vcc lock out write protect. In order to prevent data corruption and inadvertent write operations during power up, a Power On Reset (POR) circuit is implemented. Untill the Vcc voltage has reached the POR threshold value, the internal reset is active: all operations are disabled and the device will not respond to any command. In the same way, when Vcc drops down from the operating voltage to below the POR threshold value, all operations are disabled and the device will not respond to any command. A stable Vcc must be applied before applying any logic signal.

SIGNALS DESCRIPTION

Serial Clock (SCL). The SCL input pin is used to synchronize all data in and out of the memory. A resistor can be connected from the SCL line to Vcc to act as a pull up (see Figure 3)

Serial Data (SDA). The SDA pin is bi-directional and is used to transfer data in or out of the memory. It is an open drain output that may be wire-OR'ed with other open drain or open collector signals on the bus. A resistor must be connected from the SDA bus line to V_{CC} to act as pull up (see Figure 3).

Write Control (WC). The Write Control feature \overline{WC} is useful to protect the contents of the memory from any erroneous erase/write cycle. The Write Control signal is used to enable (\overline{WC} at V_{IH}) or disable (\overline{WC} at V_{IL}) the internal write protection. When pin \overline{WC} is unconnected, the \overline{WC} input is internally read as V_{IL} (see Table 5).

When \overline{WC} = '1', Device Select and Address bytes are acknowledged; Data bytes are not acknowledged.

Refer to the AN404 Application Note for more detailed information about Write Control feature.

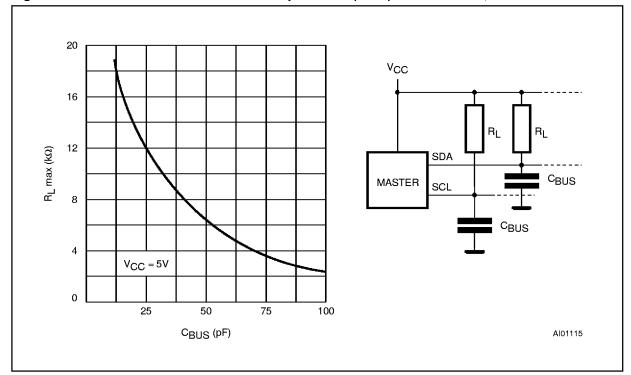


Figure 3. Maximum R_L Value versus Bus Capacitance (C_{BUS}) for an I^2C Bus, $f_C = 400 \text{kHz}$

DEVICE OPERATION

I²C Bus Background

The Memory supports the extended addressing I²C protocol. This protocol defines any device that sends data onto the bus as a transmitter and any device that reads the data as a receiver. The device that controls the data transfer is known as the master and the other as the slave. The master will always initiate a data transfer and will provide the serial clock for synchronisation. The Memory is always a slave device in all communications.

Start Condition. START is identified by a high to low transition of the SDA line while the clock SCL is stable in the high state. A START condition must precede any command for data transfer. Except during a programming cycle, the Memory continuously monitors the SDA and SCL signals for a START condition and will not respond unless one is given.

Stop Condition. STOP is identified by a low to high transition of the SDA line while the clock SCL is stable in the high state. A STOP condition terminates communication between the Memory and the bus master. A STOP condition at the end of a Read command forces the standby state. A STOP condi-

tion at the end of a Write command triggers the internal EEPROM write cycle.

Acknowledge Bit (ACK). An acknowledge signal is used to indicate a successful data transfer. The bus transmitter, either master or slave, will release the SDA bus after sending 8 bits of data. During the 9th clock pulse the receiver pulls the SDA bus low to acknowledge the receipt of the 8 bits of data.

Data Input. During data input the Memory samples the SDA bus signal on the rising edge of the clock SCL. For correct device operation the SDA signal must be stable during the clock low to high transition and the data must change ONLY when the SCL line is low.

Device Selection. To start communication between the bus master and the slave Memory, the master must initiate a START condition. The 8 bits sent after a START condition are made up of a device select of 4 bits that identifies the device type, then 3 bits (at 000) and one bit for a READ (RW = 1) or WRITE (RW = 0) operation. There are two modes both for read and write. These are summarised in Table 4 and described hereafter. A communication between the master and the slave is ended with a STOP condition.

Table 5. Input Parameters ⁽¹⁾ ($T_A = 25 \, ^{\circ}C$, $f = 400 \, kHz$)

Symbol	Parameter	Test Condition	Min	Max	Unit
C _{IN}	Input Capacitance (SDA)			8	pF
C _{IN}	Input Capacitance (other pins)			6	pF
ZwcL	WC Input Impedance	$V_{IN} \le 0.3 \ V_{CC}$	5	20	kΩ
Z _{WCH}	WC Input Impedance	$V_{IN} \ge 0.7 \ V_{CC}$	500		kΩ
t LP	Low-pass filter input time constant (SDA and SCL)			100	ns

Note: 1. Sampled only, not 100% tested.

Table 6. DC Characteristics ($T_A = 0$ to 70° C or -40 to 85° C; $V_{CC} = 4.5V$ to 5.5V, 2.5 to 5.5V or 1.8V to 5.5V)

Symbol	Parameter	Test Condition	Min	Max	Unit
lu	Input Leakage Current (SCL, SDA)	0V ≤ V _{IN} ≤ V _{CC}		±2	μΑ
ILO	Output Leakage Current	0V ≤ V _{OUT} ≤ V _{CC} SDA in Hi-Z		±2	μΑ
	Supply Current	V _{CC} = 5V, f _C = 400kHz (Rise/Fall time < 30ns)		3	mA
Icc	Supply Current (-W series)	V_{CC} = 2.5V, f_C = 400kHz (Rise/Fall time < 30ns)		t.b.c.	mA
	Supply Current (-R series)	V_{CC} = 1.8V, f_C = 400kHz (Rise/Fall time < 30ns)		t.b.c.	mA
Icc ₁	Supply Current, Standby	$\begin{array}{c} V_{\text{IN}} = V_{\text{SS}} \text{ or } V_{\text{CC}}, \\ V_{\text{CC}} = 5V \end{array}$		100	μΑ
1001	Supply Sulfont, Stallasy	$V_{IN} = V_{SS}$ or V_{CC} , $V_{CC} = 5V$, $f_C = 400$ kHz		300	μΑ
Icc2	Supply Current, Standby	$V_{\text{IN}} = V_{\text{SS}} \text{ or } V_{\text{CC}},$ $V_{\text{CC}} = 2.5 V$		t.b.c.	μΑ
1002	(-W series)	$V_{IN} = V_{SS}$ or V_{CC} , $V_{CC} = 2.5V$, $f_C = 400kHz$		t.b.c.	μΑ
Іссз	Supply Current, Standby	$V_{IN} = V_{SS} \text{ or } V_{CC},$ $V_{CC} = 1.8V$		t.b.c.	μΑ
ICCS	(-R series)	$V_{IN} = V_{SS}$ or V_{CC} , $V_{CC} = 1.8V$, $f_C = 400kHz$		t.b.c.	μΑ
V _{IL}	Input Low Voltage (SCL, SDA)		-0.3	0.3 V _{CC}	٧
V _{IH}	Input High Voltage (SCL, SDA)		0.7 V _{CC}	V _{CC} + 1	٧
V _{IL}	Input Low Voltage (WC)		-0.3	0.5	٧
V _{IH}	Input High Voltage (WC)		V _{CC} - 0.5	V _{CC} + 1	٧
	Output Low Voltage	I _{OL} = 3mA, V _{CC} = 5V		0.4	٧
V _{OL}	Output Low Voltage (-W series)	I _{OL} = t.b.c., V _{CC} = 2.5V		t.b.c.	٧
	Output Low Voltage (-R series)	I _{OL} = t.b.c., V _{CC} = 1.8V		t.b.c.	٧

Note: t.b.c. stands for "to be characterized".

Table 7. AC Characteristics

 $(T_A = 0 \text{ to } 70^{\circ}\text{C or } -40 \text{ to } 85^{\circ}\text{C}; \ V_{CC} = 4.5\text{V to } 5.5\text{V}, 2.5 \text{ to } 5.5\text{V or } 1.8\text{V to } 5.5\text{V})$

Symbol	Alt	Parameter	Min	Max	Unit
t _{CH1CH2}	t _R	Clock Rise Time		300	ns
t _{CL1CL2}	t _F	Clock Fall Time		300	ns
t _{DH1DH2} (1)	t _R	SDA Rise Time	20	300	ns
t _{DL1DL2} (1)	t _F	SDA Fall Time	20	300	ns
t _{CHDX} (2)	tsu:sta	Clock High to Input Transition	600		ns
t _{CHCL}	t _{HIGH}	Clock Pulse Width High	600		ns
tolcl	thd:sta	Input Low to Clock Low (START)	600		ns
t _{CLDX}	thd:dat	Clock Low to Input Transition	0		μs
tclch	tLOW	Clock Pulse Width Low	1.3		μs
t _{DXCX}	t _{SU:DAT}	Input Transition to Clock Transition	100		ns
t _{CHDH}	tsu:sto	Clock High to Input High (STOP)	600		ns
t _{DHDL}	t _{BUF}	Input High to Input Low (Bus Free)	1.3		μs
t _{CLQV} (3)	t _{AA}	Clock Low to Next Data Out Valid	200	900	ns
tcLQX	t _{DH}	Data Out Hold Time	200		ns
f _C	f _{SCL}	Clock Frequency		400	kHz
tw	twR	Write Time		10	ms

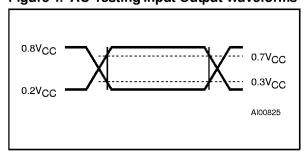
Notes: 1. Sampled only, not 100% tested.
2. For a reSTART condition, or following a write cycle.

3. The minimum value delays the falling/rising edge of SDA away from SCL = 1 in order to avoid unwanted START and/or STOP conditions.

Table 8. AC Measurement Conditions

Input Rise and Fall Times	≤ 50ns
Input Pulse Voltages	0.2V _{CC} to 0.8V _{CC}
Input and Output Timing Ref. Voltages	0.3V _{CC} to 0.7V _{CC}

Figure 4. AC Testing Input Output Waveforms



DEVICE OPERATION (cont'd)

Memory Addressing. A data byte in the memory is addressed through 2 bytes of address information. The Most Significant Byte is sent first and the Least significant Byte is sent after. Bits b15 to b0 form the address of any byte of the memory. Bit b15 is don't care on the M24256 series. Bits b15 and b14 are don't care on the M24128 series.

Most Significant Byte

	b15	b14	b13	b12	b11	b10	b9	b8
ì	b15 is do	on't care	on M24	256 serie	es.			

Least Significant Byte

b15 and b14 are don't care on M24128 series.

b7	b6	b5	b4	b3	b2	b1	b0

Figure 5. AC Waveforms

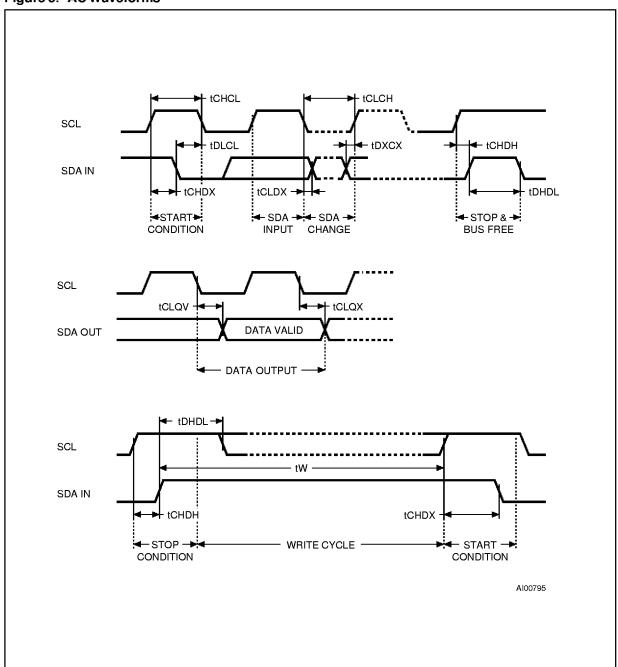
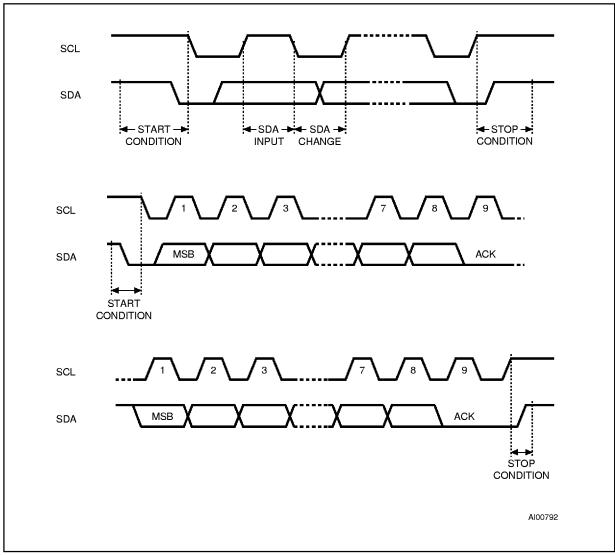


Figure 6. I²C Bus Protocol



Write Operations

Following a START condition the master sends a device select code with the $R\overline{W}$ bit reset to '0'. The Memory acknowledges this and waits for 2 bytes of address. These 2 address bytes (8 bits each) provide access to any of the memory locations. Writing in the Memory may be inhibited if input pin \overline{WC} is taken high.

Any write command with \overline{WC} = '1' (during a period of time from the START condition untill the end of the 2 Bytes Address) will not modify data and will NOT be acknowledged on data bytes, as in Figure 9.

Byte Write. In the Byte Write mode the master sends one data byte, which is acknowledged by the

Memory. The master then terminates the transfer by generating a STOP condition.

Page Write. The Page Write mode allows up to 64 bytes to be written in a single write cycle, provided that they are all located in the same row of 64 bytes in the memory, that is the same Address bits (b14 to b6). The master sends one up to 64 bytes of data, which are each acknowledged by the Memory. After each byte is transfered, the internal byte address counter (6 Least Significant Bits only) is incremented. The transfer is terminated by the master generating a STOP condition. Care must be taken to avoid address counter 'roll-over' which could result in data being overwritten. Note that for any write mode, the generation by the master of the STOP condition starts the internal memory pro-

477

gram cycle. This STOP condition will trigger an internal memory program cycle only if the STOP condition is internally decoded right after the ACK bit; any STOP condition decoded out of this "10th bit" time slot will not trigger the internal programming cycle. All inputs are disabled until the completion of this cycle and the Memory will not respond to any request.

Minimizing System Delay by Polling On ACK. During the internal Write cycle, the Memory disables itself from the bus in order to copy the data from the internal latches to the memory cells. The maximum value of the Write time (tw) is given in the Table 8, this timing value may be reduced by an ACK polling sequence issued by the master.

The sequence is:

- Initial condition: a Write is in progress (see Figure
- Step 1: the Master issues a START condition followed by a Device Select byte. (1st byte of the new instruction)
- Step 2: if the Memory is internally writing, no ACK will be returned. The Master goes back to Step1. If the Memory has terminated the internal writing, it will issue an ACK.

The Memory is ready to receive the second part of the instruction (the first byte of this instruction was already sent during Step1).

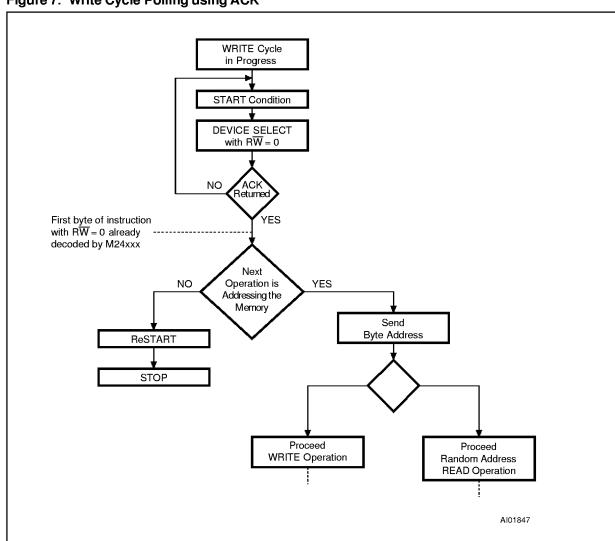


Figure 7. Write Cycle Polling using ACK

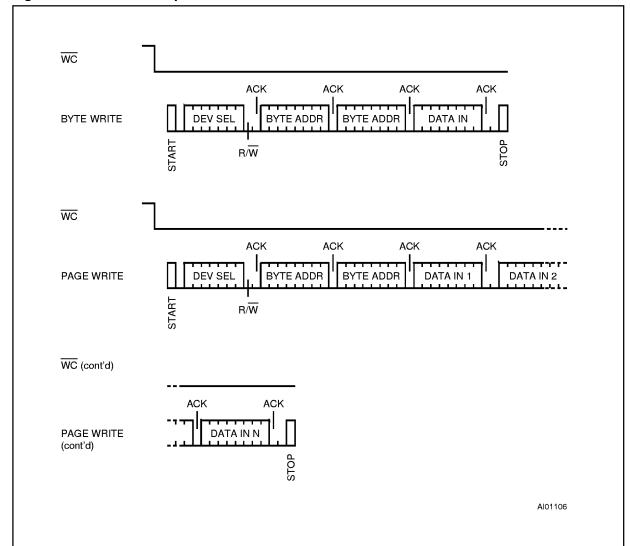


Figure 8. Write Modes Sequence with Write Control = 0

Read Operations

On delivery, the memory content is set at all "1's" (or FFh).

Current Address Read. The Memory has an internal address counter. Each time a byte is read, this counter is incremented. For the Current Address Read mode, following a START condition, the master sends a Device Select with the RW bit set to '1'. The Memory acknowledges this and outputs the byte addressed by the internal address counter. This counter is then incremented. The master does NOT acknowledge the byte output, but terminates the transfer with a STOP condition.

Random Address Read. A dummy write is performed to load the address into the address counter, see Figure 10. This is followed by another START condition from the master and the byte address repeated with the RW bit set to '1'. The Memory acknowledges this and outputs the byte addressed. The master does NOT acknowledge the byte output, but terminates the transfer with a STOP condition.

Sequential Read. This mode can be initiated with either a Current Address Read or a Random Address Read. However, in this case the master DOES acknowledge the data byte output and the Memory continues to output the next byte in se-

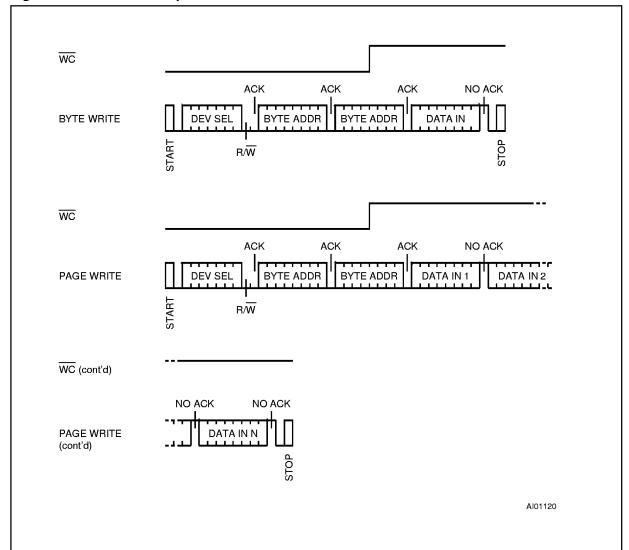


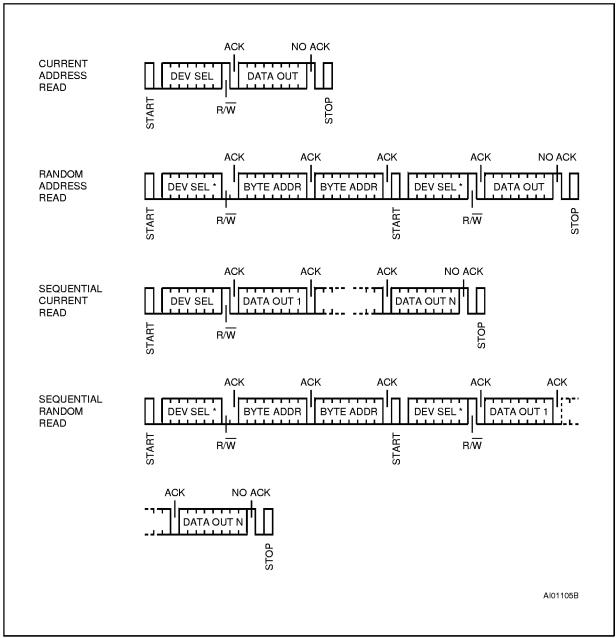
Figure 9. Write Modes Sequence with Write Control = 1

quence. To terminate the stream of bytes, the master must NOT acknowledge the last byte output, but MUST generate a STOP condition. The output data is from consecutive byte addresses, with the internal byte address counter automatically incremented after each byte output. After a count of the last memory address, the address

counter will 'roll-over' and the memory will continue to output data.

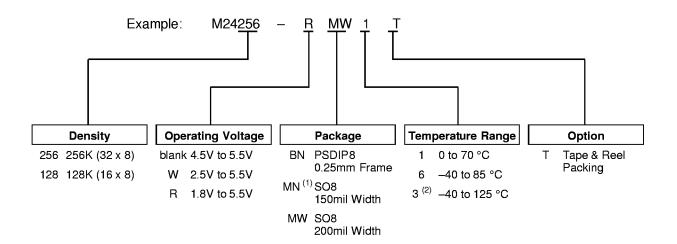
Acknowledge in Read Mode. In all read modes the Memory waits for an acknowledge during the 9th bit time. If the master does not pull the SDA line low during this time, the Memory terminates the data transfer and switch to a standby state.

Figure 10. Read Mode Sequences



Note: * The 7 Most Significant bits of DEV SEL bytes of a Random Read (1st byte and 4th byte) must be identical.

ORDERING INFORMATION SCHEME



Notes: 1. SO8, 150mil Width, package is available for M24128 series only. 2. Temperature Range on request only.

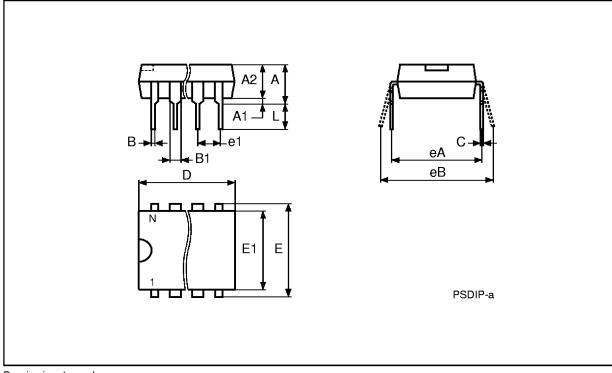
Devices are shipped from the factory with the memory content set at all "1's" (FFh).

For a list of available options (Operating Voltage, Package, etc...) or for further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.

PSDIP8 - 8 pin Plastic Skinny DIP, 0.25mm lead frame

Symb		mm			inches	
Symb	Тур	Min	Max	Тур	Min	Max
Α		3.90	5.90		0.154	0.232
A1		0.49	_		0.019	_
A2		3.30	5.30		0.130	0.209
В		0.36	0.56		0.014	0.022
B1		1.15	1.65		0.045	0.065
С		0.20	0.36		0.008	0.014
D		9.20	9.90		0.362	0.390
E	7.62	_	_	0.300	_	_
E1		6.00	6.70		0.236	0.264
e1	2.54	_	_	0.100	_	_
eA		7.80	_		0.307	_
eB			10.00			0.394
L		3.00	3.80		0.118	0.150
N		8			8	

PSDIP8

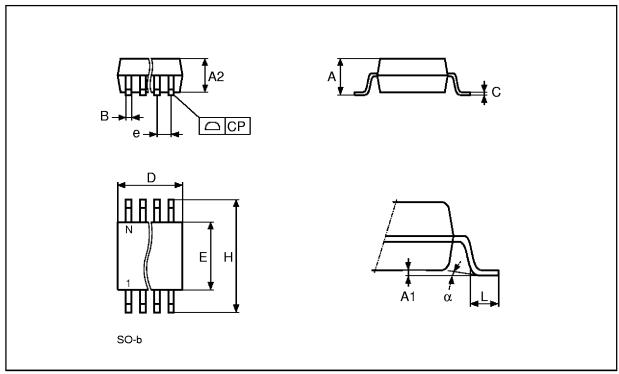


Drawing is not o scale

SO8 - 8 lead Plastic Small Outline, 150 mils body width

Symb		mm			inches	
Symb	Тур	Min	Max	Тур	Min	Max
А		1.35	1.75		0.053	0.069
A1		0.10	0.25		0.004	0.010
В		0.33	0.51		0.013	0.020
С		0.19	0.25		0.007	0.010
D		4.80	5.00		0.189	0.197
E		3.80	4.00		0.150	0.157
е	1.27	_	_	0.050	_	_
Н		5.80	6.20		0.228	0.244
h		0.25	0.50		0.010	0.020
L		0.40	0.90		0.016	0.035
α		0	8		0	8
N		8	·		8	·
CP			0.10			0.004

SO8a

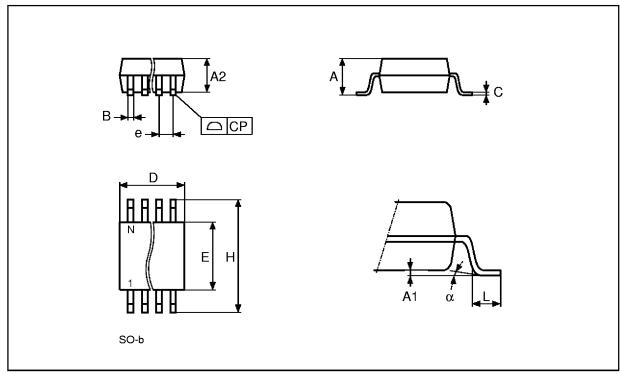


Drawing is not to scale

SO8 - 8 lead Plastic Small Outline, 200 mils body width

Symb	mm			inches		
	Тур	Min	Max	Тур	Min	Max
А			2.03			0.080
A1		0.10	0.25		0.004	0.010
A2			1.78			0.070
В		0.35	0.45		0.014	0.018
С	0.20	_	_	0.008	_	_
D		5.15	5.35		0.203	0.211
E		5.20	5.40		0.205	0.213
е	1.27	-	-	0.050	_	-
Н		7.70	8.10		0.303	0.319
L		0.50	0.80		0.020	0.031
α		0°	10°		0°	10°
N		8			8	
СР			0.10			0.004

SO8b



Drawing is not to scale